TOSHIBA Photocoupler GaAs IRed & Photo-Transistor

4N25(Short),4N25A(Short),4N26(Short),4N27(Short),4N28(Short)

AC Line / Digital Logic Isolator.

Digital Logic / Digital Logic Isolator.

Telephone Line Receiver.

Twisted Pair Line Receiver

High Frequency Power Supply Feedback Control.

Relay Contact Monitor.

The TOSHIBA 4N25 (Short) through 4N28 (Short) consists of a gallium arsenide infrared emitting diode coupled with a silicon phototransistor in a dual in–line package.

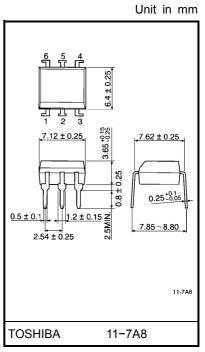
• Switching speeds: 3µs (typ.)

• DC current transfer ratio: 100% (typ.)

• Isolation resistance: $10^{11}\Omega$ (min.)

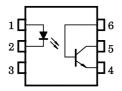
• Isolation voltage: 2500Vrms (min.)

• UL recognized: UL1577, file No. E67349



Weight: 0.4g

Pin Configurations(top view)



1:ANODE

2: CATHODE

3 : N.C.

4:EMITTER

5 : COLLECTOR

6 : BASE



Maximum Ratings (Ta = 25°C)

	Characteristic	Symbol	Rating	Unit
	Forward current (continuous)	IF	80	mA
	Forward current derating	ΔI _F / °C	1.07 (*)	mA / °C
Ω	Peak forward current (Note 1)	I _{PF}	3	Α
LED	Power dissipation	P _D	150	mW
	Power dissipation derating	ΔP _D / °C	2.0 (*)	mW / °C
	Reverse voltage	V _R	3	V
	Collector-emitter voltage	BV _{CEO}	30	V
	Collector-base voltage	BV _{CBO}	70	V
Detector	Emitter–collector voltage	BV _{ECO}	7	V
	Collector current (continuous)	IC	100	mA
	Power dissipation	PC	150	mW
	Power dissipation derating	ΔP _C / °C	2.0 (*)	mW / °C
	Storage temperature range	T _{stg}	-55~150	°C
_	Operating temperature range	T _{opr}	-55~100	°C
Coupled	Lead soldering temperature (10s)	T _{sol}	260	°C
	Total package power dissipation	P _T	250	mW
	Total package power dissipation derating	ΔP _T / °C	3.3 (*)	mW / °C

(Note 1) Pulse width 300µs, 2% duty cycle.

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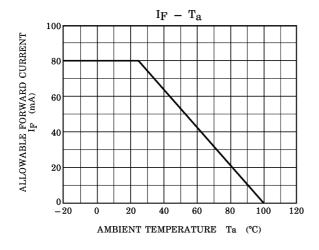
^(*) Above 25°C ambient.

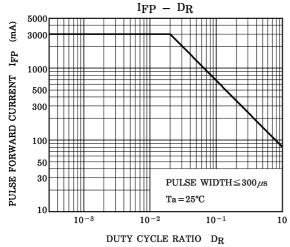


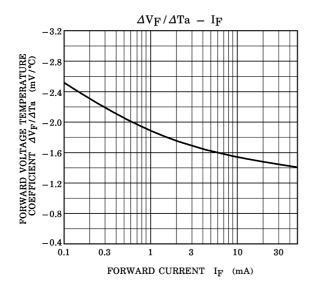
Electrical Characteristics (Ta = 25°C)

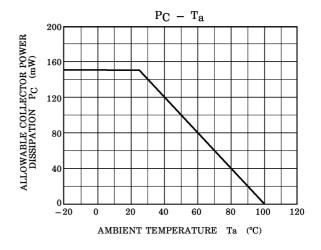
Characteristic			Symbol	Test Condition	Min.	Тур.	Max.	Unit
LED	Forward voltage		V _F	I _F = 10 mA	_	1.15	1.5	V
	Reverse current		I _R	V _R = 3 V	_	_	100	μA
	Capacitance		C _D	V = 0, f = 1 MHz	_	30	_	pF
Detector	DC forward current gain		h _{FE}	V _{CE} = 5V, I _C = 500 μA	_	200	_	_
	Collector–emitter breakdown voltage		V (BR) CEO	I _C = 1 mA, I _F = 0	30	_	_	V
	Collector-base breakdown voltage		V (BR) CBO	Ι _C = 100 μΑ	70	_	_	V
	Emitter–collector breakdown voltage		V (BR) ECO	ΙΕ = 100 μΑ	7	_	_	V
	Collector dark current		I _{CEO}	V _{CE} = 10 V	_	1	50	nA
	Collector dark current		I _{CBO}	V _{CB} = 10 V	_	0.1	20	nA
	Collector-emitter capacitance		C _{CE}	V = 0, f = 1 MHz	_	10	_	pF
pe	Current transfer ratio		I _C / I _F	I _F = 10 mA, V _{CE} = 10 V	20	100	_	%
	Collector–emitter saturation voltage		V _{CE} (sat)	I _F = 50 mA, I _C = 2 mA	_	0.1	0.5	V
	Capacitance input to output		Cs	V _S = 0, f = 1 MHz	_	0.8	_	pF
	Isolation resistance		R _S	V _S = 500 V, R.H. ≤ 60 %	10 ¹¹	_	_	Ω
			BVS	AC, 1 minute	2500	_	_	Vrms
Coupled	Isolation voltage	4N25, 4N25A	BV _S (*)	AC, peak	2500	_	_	Vpk
ŏ		4N26, 4N27			1500	_	_	
		4N28			500	_	_	
		4N25A		AC, 1 second	1775	_	_	Vrms
	Rise / fall time		t _r / t _f	V_{CE} = 10 V, I_{C} = 2 mA R_{L} = 100 Ω	_	2	_	μs
	Rise / fall time		t _r / t _f	V_{CB} = 10 V, I_{CB} = 50 μ A R_L = 100 Ω		200	_	ns

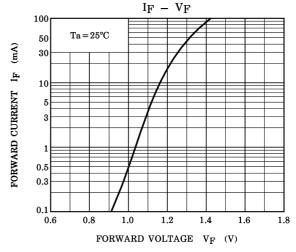
^(*) JEDEC registered minimum BV_S, however, TOSHIBA specifies a minimum BV_S of 2500 Vrms, 1 minute.

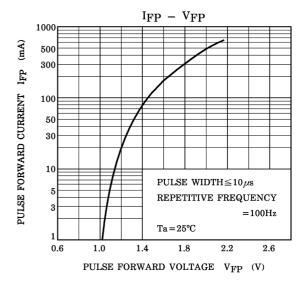




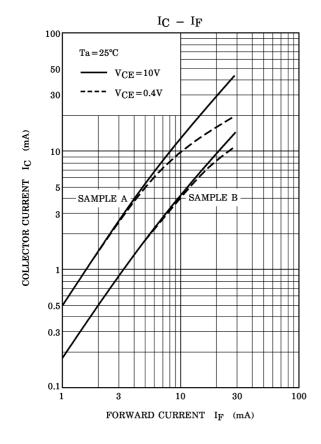


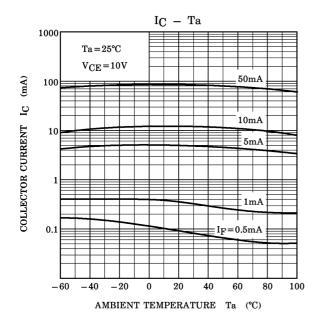


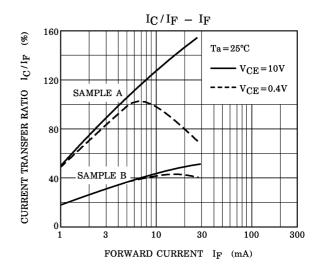


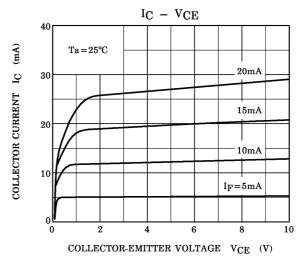


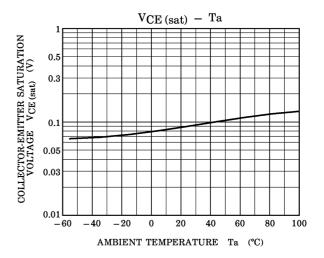
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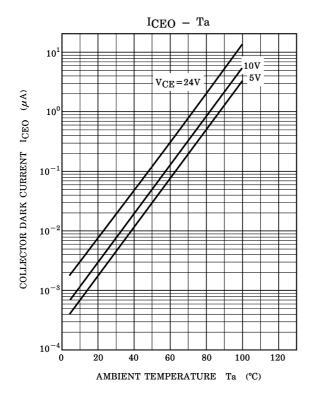


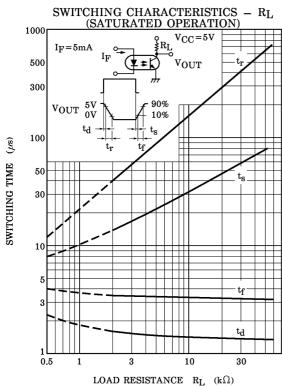


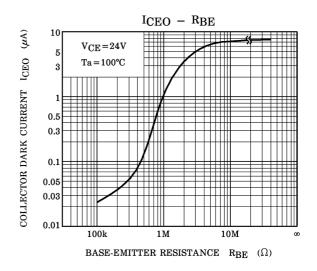


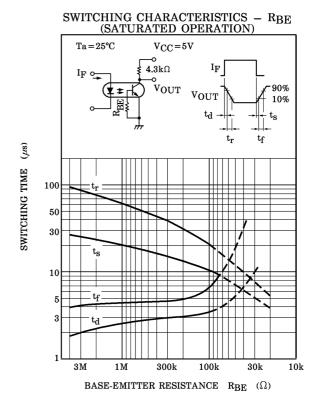












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